Naming system

Type designation thyristor and diode modules

Circuit
TT = with 2 thyristors
TD = with 1 thyristor and 1 diode
DD = with 2 diodes
ND = with 1 diode
DZ = with 1 diode
TZ = with 1 thyristor

Average on-state current
500 = ITAV, IFAV

N = phase control device
S = fast device

Blocking voltage
16 = V_{RRM}, V_{DRM}/100

_TIM = baseplate with pre-applied Thermal Interface Material (TIM)
-K = design with common cathode
-A = design with common anode
F = 1000V/µs critical rise of off-state (du/dt)
O = no guaranteed turn-off time
K = mechanical construction: pressure contact technology
S = mechanical construction: solder technology